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IIRW 2018 Table of Contents

IIRW 2018 Committees vi

IIRW 2018 Program Schedule ix

Foreword xii

Keynote xiii

IIRW 2018 Call for Papers xiv

Summaries of Invited Papers xv

Technical Papers

Self-Heating Effects on Hot Carrier Degradation and Its Impact on Ring-Oscillator Reliability 1
P. Paliwoda, Z. Chbili, A. Kerber, T. Nigam, D. Singh, K. Nagahiro, P. P Manik, S. Cimino, and D. Misra

New Insights on Device Level TDDB at GHz Speed in Advanced CMOS Nodes 5
M. Arabi, X. Federspiel, F.Cacho, M.Rafik, A-P.Nguyen, X.Garros, and G.Ghibaudo

Off-State Impact on FDSOI Ring Oscillator Degradation under High Voltage Stress 10
Jens Trommer, Viktor Havel, Talha Chohan, Furqan Mehmood, Stefan Slesazeck, Gernot Krause, Germain Bossu, Wafa Arfaoui, Armin Mühlhoff, and T. Mikolajick

FDSOI Mosfet Gate Dielectric Breakdown Vd Dependancy 15
Xavier Federspiel, Melissa Arabi, Florian Cacho, Mustapha Rafik, and Antoine Cros

Correlated Defect Creation in HfO_2 Films 19
Jack Strand and Alexander Shluger

Distribution Function Based Simulations of Hot-Carrier Degradation in Nanowire FETs 21
Michiel Vandemaele, Ben Kaczer, Zlatan Stanojević, Stanislav Tyaginov, Alexander Makarov, Adrian Chasin, Hans Mertens, Dimitri Linten, and Guido Groeseneken

Voltage- and Temperature-Dependent Degradation of AIN/GaN High Electron Mobility Transistors 25
Tobias Kemmer, Michael Dammann, Martina Baeumler, Peter Brückner, Helmer Konstanzer, Rüdiger Quay, and Oliver Ambacher

On the Impact of the Gate Metal Work-Function on the Charge Trapping Component of BTI 31
J. Franco, Z. Wu, G. Rzepa, L. -Å Ragnarsson, H. Dekkers, A. Vandooren, G. Groeseneken, N. Horiguchi, N. Collaert, D. Linten, T. Grasser, and B. Kaczer

Improved PBTI Reliability in Junction-Less nFET Fabricated at Low Thermal Budget for 3D Sequential Integration 35
Zhicheng Wu, Jacopo Franco, Anne Vandooren, Ben Kaczer, Philippe Roussel, G. Rzepa, T. Grasser, Dimitri Linten, and Guido Groeseneken

Border Trap Based Modeling of SiC Transistor Transfer Characteristics..... 39
S. E. Tyaginov, M. Jech, G. Rzepa, A. Grill, A. -M. El-Sayed, G. Pobegen, A. Makarov, and T. Grasser

Cross-Temperature Effects of Program and Read Operations in 2D and 3D NAND Flash Memories..... 44
Cristian Zambelli, Luca Crippa, Rino Micheloni, and Piero Olivo

Identifying Defects Responsible for Leakage Currents in Thin Dielectric Films..... 48
Ryan J. Waskiewicz, Elias B. Frantz, Patrick M. Lenahan, Sean W. King, Nicholas J. Harmon, and Michael E. Flatté

Self-Heating Effect in Silicon-Germanium Heterostructure Bipolar Transistors in Stress and Operating Conditions 52
Francesco Maria Puglisi, Marco Ghillini, Luca Larcher, and Paolo Pavan

Regular Posters

Reliability of High Speed Photodetector for Silicon Photonic Applications..... 57
F. Sy, Q. Rafhay, C. Besset, G. Beylier, P. Grosse, D. Roy, and J.-E. Broquin

Multiple Modes of Electromigration Failure in SAC Solder Alloys..... 61
Deborah Noble, Matthew Ring, and J. R. Lloyd

Gate-to-via Ratio Design for Reliability..... 65
T. L. Tan, P. Zhou, L. Cao, P. Y. Tan, P. Paliwoda, and C. W. Eng

Aging Control of Power Amplifier using Power Detector 68
R. Lajmi, F. Cacho, V. Knopik, P. Cathelin, J. Lugo, P. Benech, E. Lauga Larroze, S. Bourdel, and X. Federspiel

Gate Oxide Degradation Assessment by Electrical Stress and Capacitance Measurements 72
Dann Morillon, Pascal Masson, Franck Julien, Philippe Lorenzini, Jerome Goy, Clement Pribat, Olivier Gourhant, Thibault Kempf, Jean-Luc Ogier, Alexandre Villaret, Giada Ghezzi, Nathalie Cherault, and Stephan Niel

New Electromigration Model and Its Potential Application on Degradation Simulation for FinFET SRAM 76
Rui Zhang, Kexin Yang, Taizhi Liu, and Linda Milor

Investigation of the Effects of Pulsed Direct Current at Low Frequencies on the Electromigration Lifetime..... 81
Jennifer M. Passage, Sophia Rogalskyj, Nabihah Azhari, Eric Wilcox, and J. R. Lloyd

Process Optimization in IMD Deposition: A Sucessful Application of Isothermal Fast Wafer-Level Electromigration..... 85
G. Yao, Z.G. Han, H. K. Yap, F. P. Yuen, C. P. Tan, P. Y. Tan, P. Paliwoda, and C. W. Eng

Relevance of Off-State NBTI Degradation in Depletion HVNMOS Transistor for Power Application..... 88
Marc Strasser, Roberta Stradiotto, Stefano Aresu, Katja Puschkarsky, Holger Poehle, and Wolfgang Gustin

Synaptic Behavior of Nanoscale ReRAM Devices for the Implementation in a Dynamic Neural Network Array 92
Karsten Beckmann, Wilkie Olin-Ammentorp, Sierra Russell, Nadia Suguitan, Chris Hobbs, Martin Rodgers, Nathaniel C. Cady, Garrett S. Rose, and Joseph Van Nostrand

Fast Power-Temperature Cycling of BEOL Test Structures for Power Devices 96
Matt Ring, Bill Cowell, Darren Moore, and Jeff Gambino

Aging Investigation of Digital Circuit using In-Situ Monitor..... 100
R. Shah, F. Cacho, R. Lajmi, and L. Anghel

Open Poster

Lifetime Estimation Using Ring Oscillators for Prediction in FinFET Technology 104
Shu-han Hsu, Kexin Yang, Rui Zhang, and Linda Milor

Summaries of Tutorials 108

Discussion Group Slides 109

Group Photos 126

Author Index 130